PHPT60406NY

40 V, 6 A NPN high power bipolar transistor

8 December 2014

Product data sheet

1. General description

NPN high power bipolar transistor in a SOT669 (LFPAK56) Surface-Mounted Device (SMD) power plastic package.

PNP complement: PHPT60406PY

2. Features and benefits

- High thermal power dissipation capability
- High temperature applications up to 175 °C
- Reduced Printed Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified.

3. Applications

- Power management
- Load switch
- Linear mode voltage regulator
- Backlighting applications
- Relay replacement
- Motor drive

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	40	V
I _C	collector current		-	-	6	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	14	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = 6 A; I_B = 600 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$; T_{amb} = 25 °C	-	45	60	mΩ



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter	mb	C
2	E	emitter		в
3	Е	emitter	[d	, N
4	В	base	وققق	E sym123
mb	С	collector	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	Symiles

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PHPT60406NY	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669		

7. Marking

Table 4. Marking codes

Type number	Marking code
PHPT60406NY	0406NAB

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

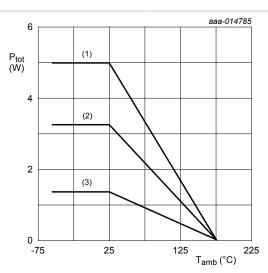
Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	40	V
V _{CEO}	collector-emitter voltage	open base		-	40	V
V _{EBO}	emitter-base voltage	open collector		-	7	V
I _C	collector current			-	6	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	14	Α
I _B	base current			-	800	mA
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	1.4	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	1.35	W
			[2]	-	3.25	W
			[3]	-	5	W
			[4]	-	25	W
Tj	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB); single-sided copper; tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB; single-sided copper; tin-plated and mounting pad for collector 6 cm².

^[3] Device mounted on a ceramic PCB; Al₂O₃, standard footprint.

^[4] Power dissipation from junction to mounting base.



- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
uily a)	thermal resistance		[1]	-	-	111	K/W
	from junction to		<u>[2]</u>	-	-	46	K/W
	ambient		<u>[3]</u>	-	-	30	K/W
R _{th(j-mb)}	thermal resistance from junction to mounting base			-	-	6	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 6 cm².
- [3] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.

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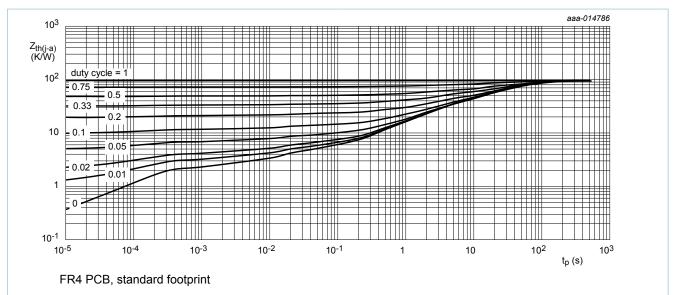


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

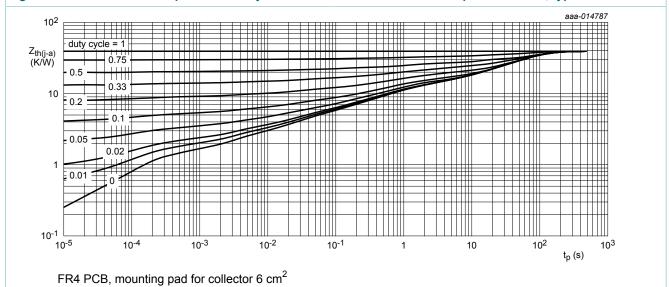


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

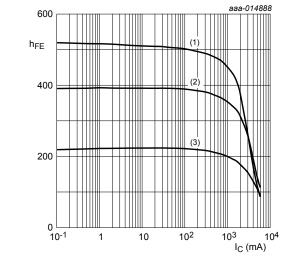
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
СВО	collector-base cut-off	$V_{CB} = 32 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	100	nA
	current	$V_{CB} = 32 \text{ V}; I_E = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	-	50	μA
CES	collector-emitter cut-off current	$V_{CE} = 32 \text{ V}; V_{BE} = 0 \text{ V}; T_{amb} = 25 \text{ °C}$	-	-	100	nA
ЕВО	emitter-base cut-off current	V _{EB} = 7 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE} DC curren	DC current gain	V_{CE} = 2 V; I_{C} = 500 mA; T_{amb} = 25 °C	230	350	-	
		$V_{CE} = 2 \text{ V}; I_{C} = 1 \text{ A}; t_{p} \le 300 \mu\text{s};$ $\delta \le 0.02; T_{amb} = 25 ^{\circ}\text{C}$	220	335	-	
		$V_{CE} = 2 \text{ V}; I_{C} = 3 \text{ A}; t_{p} \le 300 \mu\text{s};$ $\delta \le 0.02; T_{amb} = 25 ^{\circ}\text{C}$	150	235	-	
		V_{CE} = 2 V; I_{C} = 6 A; t_{p} ≤ 300 µs; δ ≤ 0.02; T_{amb} = 25 °C; pulsed	60	95	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = 1 A; I_B = 50 mA; $t_p \le$ 300 μs; $δ \le$ 0.02; T_{amb} = 25 °C; pulsed	-	45	70	mV
		$I_C = 3 \text{ A}; I_B = 300 \text{ mA}; \text{ pulsed};$ $t_p \le 300 \mu\text{s}; \delta \le 0.02; T_{amb} = 25 ^{\circ}\text{C}$	-	110	170	mV
		I_C = 6 A; I_B = 300 mA; pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	240	380	mV
R _{CEsat}	collector-emitter saturation resistance	I_C = 6 A; I_B = 600 mA; pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	45	60	mΩ
V_{BEsat}	base-emitter saturation voltage	I_C = 1 A; I_B = 50 mA; pulsed; $t_p \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	0.85	1	V
		I_{C} = 3 A; I_{B} = 300 mA; pulsed; $t_{p} \le$ 300 µs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	1	1.15	V
		I_C = 6 A; I_B = 300 mA; pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	1	1.2	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = 2 V; I_{C} = 0.5 A; T_{amb} = 25 °C	-	0.7	0.8	V
d	delay time	V_{CC} = 12.5 V; I_{C} = 3 A; I_{Bon} = 0.15 A;	-	10	-	ns
t _r	rise time	I_{Boff} = -0.15 A; T_{amb} = 25 °C	-	95	-	ns
on	turn-on time		-	105	-	ns
s	storage time		-	455	-	ns
ŀf	fall time		-	120	-	ns
off	turn-off time		-	575	-	ns

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _T	transition frequency	V_{CE} = 10 V; I_{C} = 500 mA; f = 100 MHz; T_{amb} = 25 °C	-	153	-	MHz
C _c	collector capacitance	V _{CB} = 10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	41	-	pF



 $V_{CE} = 2 V$

(1) $T_{amb} = 100 \, ^{\circ}C$

(2) T_{amb} = 25 °C

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig. 4. DC current gain as a function of collector current; typical values

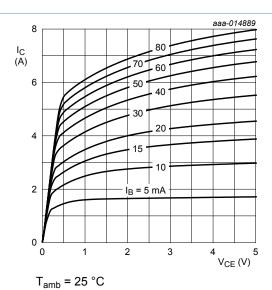
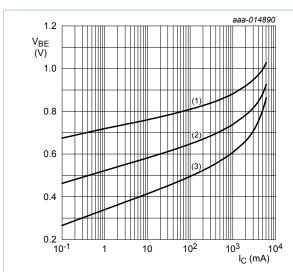


Fig. 5. Collector current as a function of collectoremitter voltage; typical values



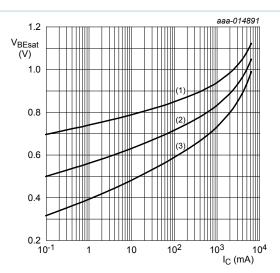
$$V_{CE} = 2 V$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb}$$
 = 100 °C





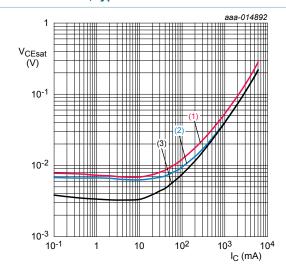
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values



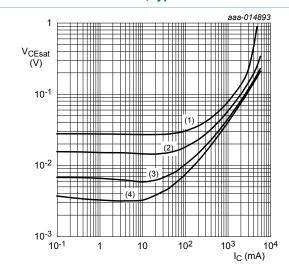
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = -55 °C$$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



(1)
$$I_C/I_B = 100$$

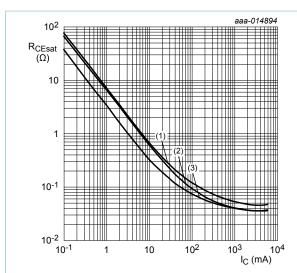
(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 20$$

$$(4) I_{\rm C}/I_{\rm B} = 10$$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

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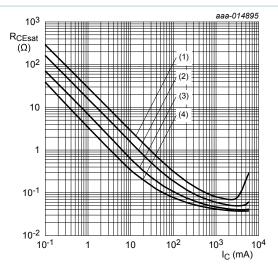
 $I_C/I_B = 20$

(1) $T_{amb} = 100 \, ^{\circ}C$

(2) T_{amb} = 25 °C

(3) $T_{amb} = -55$ °C

Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values



 T_{amb} = 25 °C

(1) $I_C/I_B = 100$

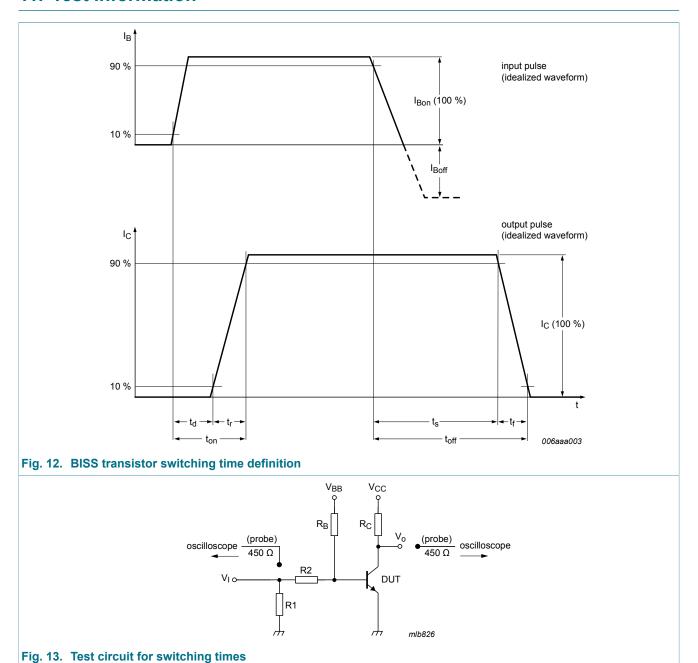
(2) $I_C/I_B = 50$

(3) $I_C/I_B = 20$

(4) $I_C/I_B = 10$

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

11. Test information



11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline

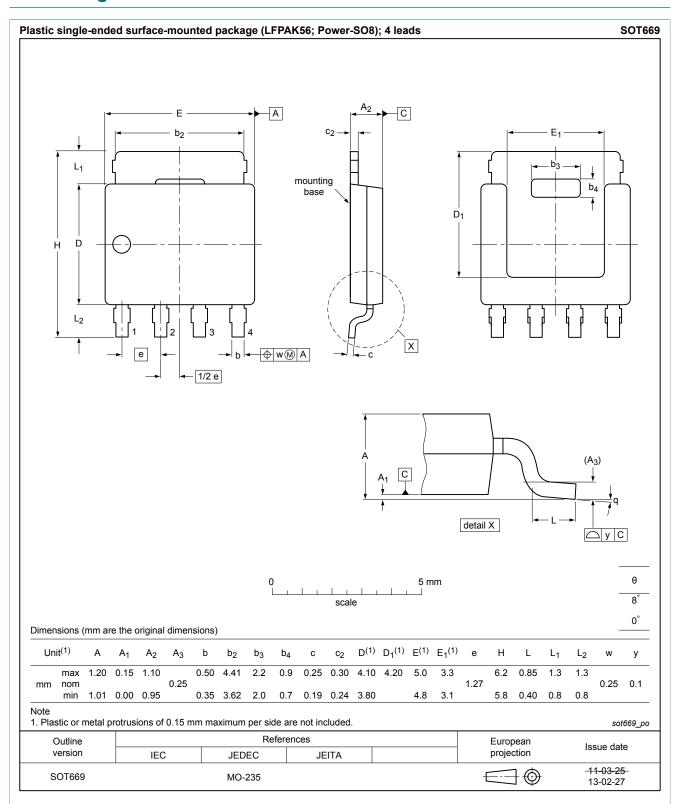
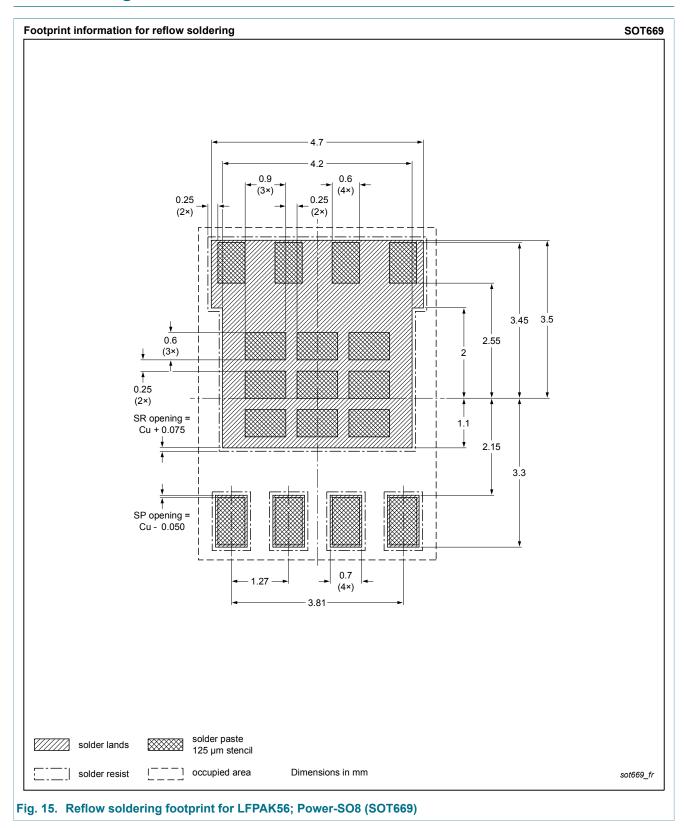


Fig. 14. Package outline LFPAK56; Power-SO8 (SOT669)

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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PHPT60406NY v.1	20141208	Product data sheet	-	-

Product data sheet

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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